

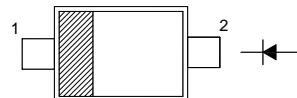
1A Surface Mount Schottky Barrier Diode

FEATURES

For use in low voltage, high frequency inverters
Free wheeling, and polarity protection applications.

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View

Simplified outline SOD-323 and symbol

MARKING: B5817WS: SJ

B5818WS: SL

B5819WS: SL

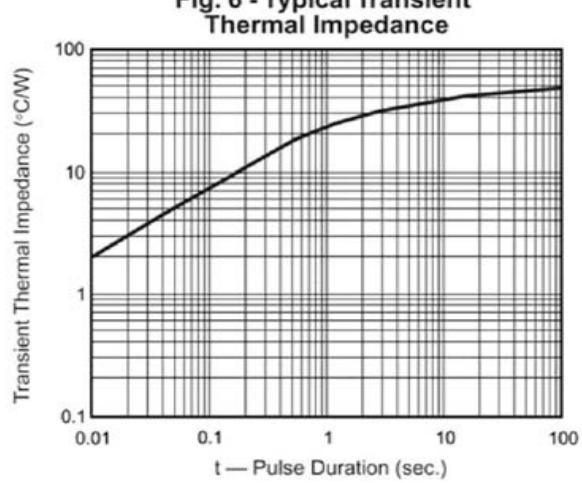
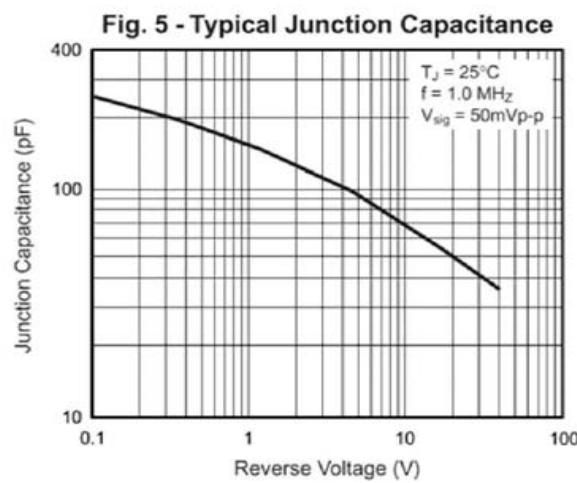
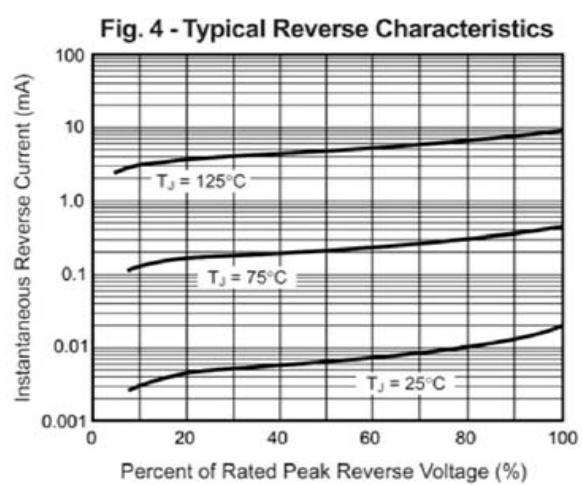
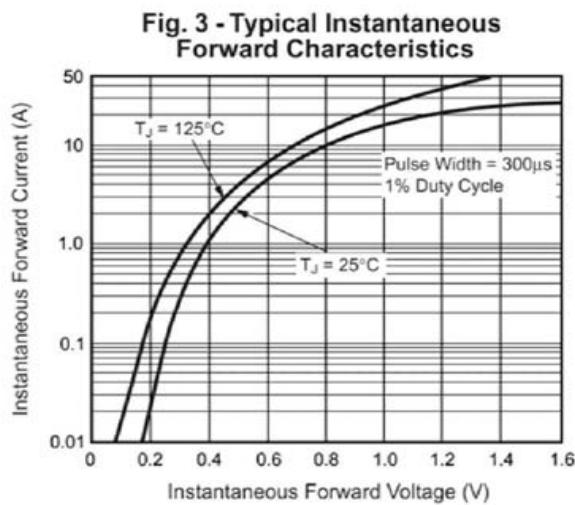
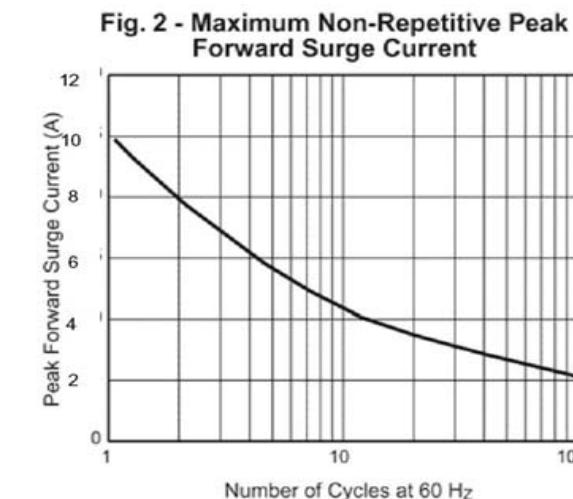
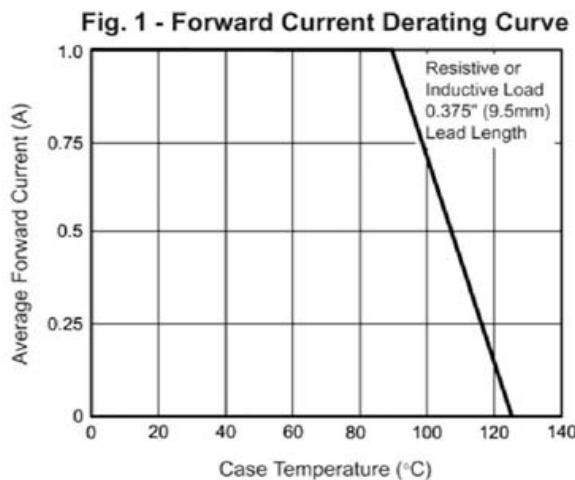
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage 1N5817WS 1N5818WS 1N5819WS	V_R	20	V
		30	
		40	
Average Forward Rectified Current	$I_{F(AV)}$	1	A
Non-Repetitive Peak Forward Surge Current ($t = 8.3 \text{ ms}$)	I_{FSM}	9	A
Power Dissipation	P_{tot}	450	mW
Operating Temperature Range	T_j	- 55 to + 125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1 \text{ mA}$ 1N5817WS 1N5818WS 1N5819WS	$V_{(BR)R}$	20	-	V
		30	-	
		40	-	
Forward Voltage at $I_F = 1 \text{ A}$ 1N5817WS 1N5818WS 1N5819WS at $I_F = 3 \text{ A}$ 1N5817WS 1N5818WS 1N5819WS	V_F	-	0.45	V
		-	0.55	
		-	0.6	
		-	0.75	
		-	0.875	
		-	0.9	
Reverse Voltage Leakage Current at $V_R = 20 \text{ V}$ 1N5817WS at $V_R = 30 \text{ V}$ 1N5818WS at $V_R = 40 \text{ V}$ 1N5819WS	I_R	-	1	mA
		-	1	
		-	1	
Total Capacitance at $V_R = 4 \text{ V}, f = 1 \text{ MHz}$	C_{tot}	-	120	pF

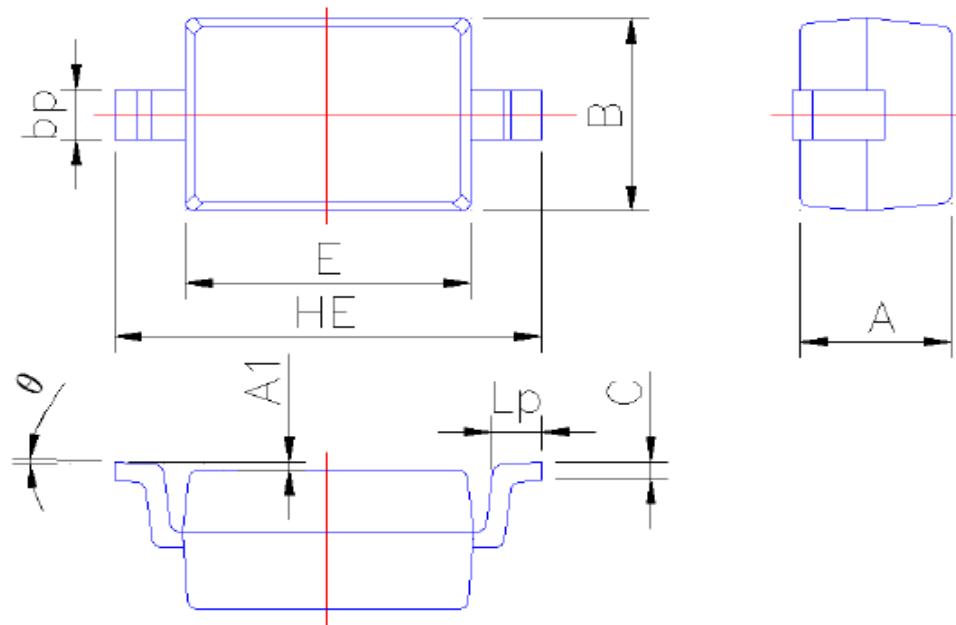
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°